



Product Change Notification



Product Group: Vishay Siliconix/ February 24, 2016/PCN SIL-0032016

Vishay Siliconix Announces Additional Copper Wire Conversion

DESCRIPTION OF CHANGE: As part of our continuous improvement package improvement program, Vishay Siliconix announces the qualification of Copper wire conversion on Low Voltage MOSFET part numbers **SI7430DP-T1-E3** and **SI7430DP-T1-GE3**.

CLASSIFICATION OF CHANGE: Material set conversion

REASON FOR CHANGE: Part of continued quality improvement program.

EXPECTED INFLUENCE ON QUALITY/RELIABILITY/PERFORMANCE: Enhancement to long-term product reliability. No changes will be made to electrical performance or datasheet parameters.

PRODUCT Category: Power MOSFETs

PART NUMBERS/SERIES/FAMILIES AFFECTED:

SI7430DP-T1-E3

SI7430DP-T1-GE3

VISHAY BRAND(s): Vishay Siliconix

TIME SCHEDULE: Shipments will begin in May 2016.

SAMPLE AVAILABILITY: Please contact your regional Vishay Sales office for sample availability.

PRODUCT IDENTIFICATION: There will be no change to part numbering. Products converted to Copper wire will have a datecode **W64Cxx** or later.

This PCN is considered approved, without further notification, unless we receive specific customer concerns before May 24, 2016 as specified by contract.

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